TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7SP97TU,TC7SP98TU

Low Voltage Single Configurable Multiple Function Gate with 3.6 V Tolerant Inputs and Outputs

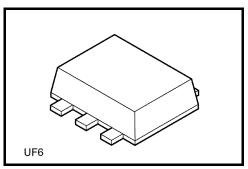
The TC7SP97,98 is a high performance CMOS multiple Function Gate which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

It independently consists of three circuits for Multiple Function Gate.

The output state is determined by seven patterns of 3-inputs. The user can choose the functions of Multiplexer, AND, OR, NAND, Schmitt Inverter, and Schmitt Buffer.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.007 g(typ)

Features

• Low-voltage operation : V_{CC} = 1.2 to 3.6 V

• High-speed operation : $t_{pd} = 8.5 \text{ ns (max)} (V_{CC} = 3.0 \text{ to } 3.6 \text{ V})$

 $t_{pd} = 12.0 \text{ ns (max) (VCC} = 2.3 \text{ to } 2.7 \text{ V)}$

• Output current : $| I_{OH} | / I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 3.0 \text{ V)}$

: $| I_{OH} | / I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 2.3 \text{ V})$

 $IOH /IOL = \pm 1.5 \text{ mA (min) (VCC} = 1.65 \text{ V)}$

• Latch-up performance : -300 mA

• ESD performance : Machine model $\geq \pm 200 \text{ V}$

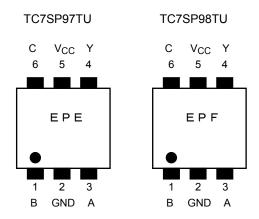
Human body model $\geq \pm 2000 \text{ V}$

Package : UF6

Power-down protection is provided on all inputs and outputs

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Pin Assignment (top view)

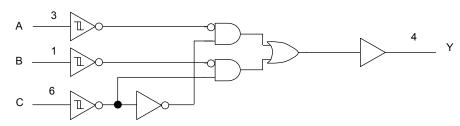


Truth Table

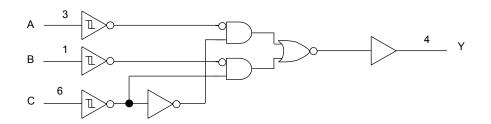
	INPUTS		OUT	ΓΡUT
	INFUIS		TC7SP97	TC7SP98
Α	В	С	Υ	Υ
L	L	L	L	Н
L	L	Н	L	Н
L	Н	L	Н	L
L	Н	Н	L	Н
Н	L	L	L	Н
Н	L	Н	Н	L
Н	Н	L	Н	L
Н	Н	Н	Н	L

System Diagram

TC7SP97



TC7SP98



Logic configrations(1/2)

Function	Input Condition	TC7SP97 Logic symbol	TC7SP98 Logic symbol	FUNCTION TABLE
SP97 AND SP98 NAND	A=INPUT B=L-Level C=INPUT Y=OUTPUT	A	A C Y	A B C Y 97 98 L L L L H L H H H H H H H H H
SP97 OR	A=H-Level B=INPUT C=INPUT	B Y	B Y	H L H H L A B C Y 97 98 H L L L H
SP98 NOR SP97	Y=OUTPUT			H L H H L H H L H L
Schmitt INV+NOR or Schmitt INV+AND SP98 Schmitt INV+OR or Schmitt INV+NAND	A=L-Level B=INPUT C=INPUT Y=OUTPUT	B OR OR C Y	B OR OR Y	A B C Y 97 98 L L L L L H L L H L H L H L H L
SP97 Schmitt INV+NAND or Schmitt INV+OR SP98 Schmitt INV+AND or Schmitt INV+AND	A=INPUT B=H-Level C=INPUT Y=OUTPUT	A OF Y OR A C T OR Y	A OF Y OR A C Y	A B C Y 97 98 L H L H L L H H L H H H L H L H H H L H L
SP97 2 to 1 Selector SP98 2 to 1 Selector+INV	A=INPUT B=INPUT C=Select Y=OUTPUT	C A B Y	C A B Y	A B C Y 97 98 L L L L H L H L H L H L H L H H H L H L

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Logic configrations(2/2)

Function	Input Condition	TC7SP97 Logic symbol	TC7SP98 Logic symbol	FUNCTION TABLE
SP97 Schmitt INV SP98 Schmitt Buffer	A=L-Level B=H-Level C=INPUT Y=OUTPUT	C Y	C Y	A B C Y 97 98 L H L H L L H H L H
SP97 Schmitt Buffer SP98 Schmitt INV	A=H-Level B=L-Level C=INPUT Y=OUTPUT	C Y	C Y	A B C Y 98 H L L L H H L H L
SP97 Schmitt Buffer SP98 Schmitt INV	A=L-Level B=INPUT C=L-Level Y=OUTPUT	В Y	В Y	A B C Y 97 98 L L L L H L H L H L
SP97 Schmitt Buffer SP98 Schmitt INV	A=H-Level B=INPUT C=L-Level Y=OUTPUT	В Y	В Y	A B C Y 97 98 H L L L H H H L H L
SP97 Schmitt Buffer SP98 Schmitt INV	A=INPUT B=L-Level C=H-Level Y=OUTPUT	A Y	AY	A B C Y 98 L L H L H H L H L

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Absolute Maximum Rating (Note1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
DC output voltage	Vout	-0.5 to 4.6 (Note2)	V
DC output voltage	VOUI	-0.5 to V _{CC} + 0.5(Note3)	
Input diode current	Ι _{ΙΚ}	-20	mA
Output diode current	I _{OK}	±20 (Note4)	mA
DC output current	lout	±25	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±25	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction. Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: $V_{CC} = 0 V$

Note 3: High or Low state. I_{OUT} absolute ratiingmust be observed.

Note 4: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Operating Range (Note1)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	1.2~3.6	V	
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	\/a	0~3.6 (Note2)	V	
Output voltage	V _{OUT}	0~V _{CC} (Note3)		
		±8.0 (Note4)		
Output current	I _{OH} /I _{OL}	±4.0 (Note5)	mA	
		±1.5 (Note6)		
Operating temperature	T _{opr}	-40~85	°C	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: $V_{CC} = 0 V$

Note 3: High or low state

Note 4: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 5: V_{CC} = 2.3~2.7 V

Note 6: $V_{CC} = 1.65 \sim 1.8 \text{ V}$



Electrical Characteristics

DC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characte	ristics	Symbol	Test Condition			Min	Max	Unit							
1		Cymbor					Max	O.III							
					1.2		1.10								
							1.20								
	H-level	V _P			1.65		1.35	V							
	i i-level	VP			2.3		1.70]							
					3.0		2.00								
Input voltage					3.6		2.20								
input voitage					1.2	0.10									
					1.4	0.20									
	Lievel				1.65	0.30		Ī ,,							
	L-level	V _N	-	_	2.3	0.50		V							
					3.0	0.70		 							
						0.80									
				1.2	0.2	0.9									
					1.4	0.2	0.9	V							
I le retenencia e calta ma					1.65	0.2	0.95								
Hysteresis voltage		V _H	_		2.3	0.3	1.0	V							
						0.3	1.2								
					3.6	0.3	1.2								
				I _{OH} = -100 μA	1.2~1.3	Vcc - 0.1	_								
				I _{OH} = -500 μA	1.4~1.6	Vcc - 0.2	_								
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -1.5 mA	1.65~1.95	Vcc - 0.3	_								
							l				I _{OH} = -4.0 mA	2.3~2.7	Vcc - 0.4	_	
Output voltage				$I_{OH} = -8.0 \text{ mA}$	3.0~3.6	2.40	_	- V -							
Output voltage				$I_{OL} = 100 \mu A$	1.2~1.3	_	0.10								
				I _{OL} = 500 μA	1.4~1.6	_	0.20								
	L-level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 3.0 mA	1.65~1.95	_	0.25								
				I _{OL} = 4.0 mA	2.3~2.7	_	0.40								
				I _{OL} = 8.0 mA	3.0~3.6	_	0.40	1							
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V	•	1.2~3.6	_	±1.5	μА							
Power-off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6	V	0	_	1.5	μА							
Quiocoat augste	ourront	1	V _{IN} = V _{CC} or GND		1.2~3.6	_	3.0								
Quiescent supply	current	Icc	$V_{CC} \le V_{IN} \le 3.6 \text{ V}$		1.2~3.6	_	±3.0	μА							
Increase in I _{CC} pe	er input	Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	100	1							

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AC Characteristics (Ta = -40 to 85°C, Input: $t_r = t_f = 3.0$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
	t _{pLH}	Figure 1, Figure 2	1.8± 0.15	1.0	21.0	
		CL = $10pF$, $R_1 = 1M \Omega$	2.5 ± 0.2	8.0	10.0	ns
	t _{pHL}	CE - 10pi (1\[- 1\lim \s2	3.3 ± 0.3	0.6	7.0	
Propagation delay time	t _{pLH}	Figure 1, Figure 2 CL = 15pF, R_L = 1M Ω	1.8± 0.15	1.0	23.0	
(A, B,C-Y)			2.5 ± 0.2	8.0	11.0	ns
(A, B,O-1)			3.3 ± 0.3	0.6	7.7	
	t _{pLH}		1.8± 0.15	1.0	27.0	
		Figure 1, Figure 2	2.5 ± 0.2	0.8	12.0	ns
		CL = 30pF, R_L = 1M Ω	3.3 ± 0.3	0.6	8.5	

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 3.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	n		Тур.	Unit
Characteristics	Syllibol	rest condition	٧	V _{CC} (V)	τyp.	Oill
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ite)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ite)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ite)	3.3	8.0	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ite)	1.8	-0.25	
Quiet output minimum dynamic $V_{\mbox{OL}}$	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ite)	2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	1		Тур.	Unit
				V _{CC} (V)		
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note)	1.8, 2.5, 3.3	30	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit

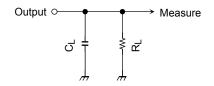
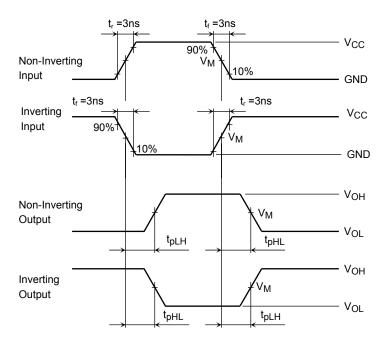


Figure 1

AC Waveform



Symbol		V _{CC}	
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V± 0.15 V
V _{IN}	V _{CC}	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2

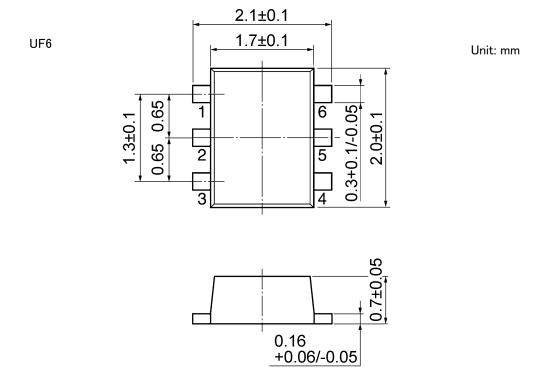
Figure 2 t_{pLH}, t_{pHL}

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2007-10-19



Package Dimensions



Weight: 0.06 g (typ.)

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